

IN THE CLAIMS:

Claim 1 (previously presented): A high frequency circuit comprising:
a transistor having a first terminal receiving an input signal and having a second terminal
and a third terminal;
a first circuit connected to said second terminal of said transistor; and
a second circuit connected to said third terminal of said transistor,
at least one of said first and second circuits comprising one of a plurality of thin film
resistors,
wherein said one or plurality of thin film resistors have a thickness smaller than three
times its skin depth at a predetermined frequency in the range of 1 MHz to 10 GHz.

Claim 2 (original): The high frequency circuit according to claim 1, wherein
said first circuit is connected between said second terminal of said transistor and a power
supply terminal receiving a power supply voltage, and
said second circuit is connected between said third terminal of said transistor and a
grounding terminal receiving a grounding potential.

Claim 3 (original): The high frequency circuit according to claim 2, wherein
at least one of said first and second circuits comprises a series connection of said one or a
plurality of thin film resistors and one or a plurality of resistors having no frequency dependency.

Claim 4 (original): The high frequency circuit according to claim 2, wherein
at least one of said first and second circuits comprises a parallel connection of one or a
plurality of thin film resistors and said one or a plurality of resistors having no frequency
dependency.

Claim 5 (original): The high frequency circuit according to claim 1, wherein
said first circuit has a feedback circuit for feeding back a signal at said second terminal of
said transistor to said first terminal, and
said feedback circuit comprises said one or plurality of thin film resistors.

Claim 6 (withdrawn): The high frequency circuit according to claim 5, further comprising
one or a plurality of other transistors,
said feedback circuit feeding back a signal at said second terminal to said first terminal
through said one or plurality of other transistors.

Claim 7 (withdrawn): The high frequency circuit according to claim 5, wherein
said feedback circuit has a feedback path for applying a part of a voltage signal at said
second terminal to said first terminal in series, and
said feedback path comprises said one or plurality of thin film resistors and one or
plurality of resistors having no frequency dependency.

Claim 8 (original): The high frequency circuit according to claim 5, wherein
said feedback circuit has a feedback path comprising a conversion portion for converting
a part of a current signal at said second terminal into a voltage signal and an application portion
for applying the voltage signal obtained by said conversion portion to said first terminal in series,
said feedback path comprising said one or plurality of thin film resistors and one or
plurality of resistors having no frequency dependency.

Claim 9 (withdrawn): The high frequency circuit according to claim 5, wherein
said feedback circuit has a feedback path comprising a conversion portion for converting
a voltage signal at said second terminal into a current signal and an application portion for
applying the current signal obtained by said conversion portion to said first terminal in parallel,
said feedback path comprising said one or plurality of thin film resistors and one or
plurality of resistors having no frequency dependency.

Claim 10 (withdrawn): The high frequency circuit according to claim 5, wherein
said feedback circuit has a feedback path for applying a part of a current signal at said
second terminal to said first terminal in parallel, and
said feedback path comprises said one or plurality of thin film resistors and one or
plurality of resistors having no frequency dependency.

Claim 11 (withdrawn): The high frequency circuit according to claim 5, wherein
said feedback circuit has a first feedback path for applying a part of a voltage signal at
said second terminal to said first terminal in series and a second feedback path for applying a
part of a current signal at said second terminal to said first terminal in parallel, and
each of said first feedback path and said second feedback path comprises said one or
plurality of thin film resistors and one or plurality of resistors having no frequency dependency.

Claim 12 (canceled)

Claim 13 (currently amended): The high frequency circuit according to claim ~~12~~ 1,
wherein said one or plurality of thin film resistors have a thickness of not more than the skin
depth at said predetermined frequency.

Claim 14 (original): The high frequency circuit according to claim 1, wherein said
transistor is a bipolar transistor.

Claim 15 (withdrawn): The high frequency circuit according to claim 1, wherein
said transistor is a field effect transistor.

Claim 16 (original): The high frequency circuit according to claim 1, wherein

said one or plurality of thin film resistors are formed of a thin film of a metal or a metal compound.

Claim 17 (original): The high frequency circuit according to claim 16, wherein
said thin film of the metal or the metal compound includes aluminum, titanium, or
tantalum.

Claim 18 (original): The high frequency circuit according to claim 3, wherein
said one or plurality of resistors having no frequency dependency are composed of a
semiconductor.

Claim 19 (original): The high frequency circuit according to claim 4, wherein
said one or plurality of resistors having no frequency dependency are composed of a
semiconductor.